

2N3055 NPN
MJ2955 PNP

**COMPLEMENTARY
SILICON POWER TRANSISTORS**



TO-3 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N3055 and MJ2955 are complementary silicon power transistors manufactured by the epitaxial base process, mounted in a hermetically sealed metal case, designed for general purpose switching and amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: ($T_C=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Continuous Base Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL		UNITS
V_{CB0}	100	V
V_{CER}	70	V
V_{CEO}	60	V
V_{EBO}	7.0	V
I_C	15	A
I_B	7.0	A
P_D	115	W
T_J, T_{stg}	-65 to +200	$^\circ\text{C}$
Θ_{JC}	1.52	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_C=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CEV}	$V_{CE}=100\text{V}, V_{EB}=1.5\text{V}$		1.0	mA
I_{CEV}	$V_{CE}=100\text{V}, V_{EB}=1.5\text{V}, T_C=150^\circ\text{C}$		5.0	mA
I_{CEO}	$V_{CE}=30\text{V}$		0.7	mA
I_{EBO}	$V_{EB}=7.0\text{V}$		5.0	mA
BV_{CEO}	$I_C=200\text{mA}$	60		V
BV_{CER}	$I_C=200\text{mA}, R_{BE}=100\Omega$	70		V
$V_{CE(SAT)}$	$I_C=4.0\text{A}, I_B=400\text{mA}$		1.1	V
$V_{CE(SAT)}$	$I_C=10\text{A}, I_B=3.3\text{A}$		3.0	V
$V_{BE(ON)}$	$V_{CE}=4.0\text{V}, I_C=4.0\text{A}$		1.5	V
h_{FE}	$V_{CE}=4.0\text{V}, I_C=4.0\text{A}$	20	70	
h_{FE}	$V_{CE}=4.0\text{V}, I_C=10\text{A}$	5.0		
h_{fe}	$V_{CE}=4.0\text{V}, I_C=1.0\text{A}, f=1.0\text{kHz}$	15	120	
f_T	$V_{CE}=10\text{V}, I_C=0.5\text{A}, f=1.0\text{MHz}$	2.5		MHz
f_{hfe}	$V_{CE}=4.0\text{V}, I_C=1.0\text{A}, f=1.0\text{kHz}$	10		kHz
$I_{s/b}$	$V_{CE}=40\text{V}, t=1.0\text{s}$	2.87		A

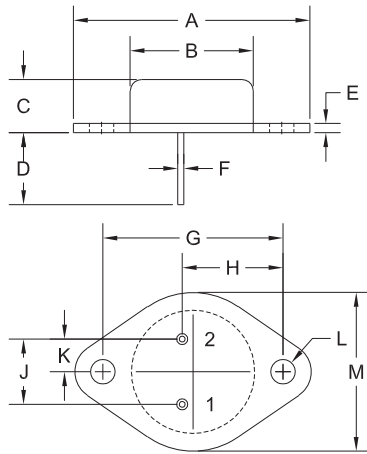
R1 (26-July 2013)

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TO-3 CASE - MECHANICAL OUTLINE



R2

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.516	1.573	38.50	39.96
B (DIA)	0.748	0.875	19.00	22.23
C	0.250	0.450	6.35	11.43
D	0.433	0.516	11.00	13.10
E	0.054	0.065	1.38	1.65
F	0.035	0.045	0.90	1.15
G	1.177	1.197	29.90	30.40
H	0.650	0.681	16.50	17.30
J	0.420	0.440	10.67	11.18
K	0.205	0.225	5.21	5.72
L (DIA)	0.151	0.172	3.84	4.36
M	0.984	1.050	25.00	26.67

TO-3 (REV: R2)

LEAD CODE:

- 1) Base
- 2) Emitter
- Case) Collector

MARKING:

FULL PART NUMBER

R1 (26-July 2013)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

Corporate Headquarters & Customer Support Team

Central Semiconductor Corp.
145 Adams Avenue
Hauppauge, NY 11788 USA
Main Tel: (631) 435-1110
Main Fax: (631) 435-1824
Support Team Fax: (631) 435-3388
www.centrasemi.com

Worldwide Field Representatives:
www.centrasemi.com/wwreps

Worldwide Distributors:
www.centrasemi.com/wwdistributors

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